

GEC 7522 VIDICON

The GEC 7522 electrostatic focus and deflection vidicon was designed to provide a small pickup tube requiring low operating power in equipment of minimum size and weight. Deflection is accomplished by a Deflectron, a revolutionary electrostatic deflection device. Resolution of 500 lines is obtained with 300 volts beam acceleration. Power requirements and operating voltages are designed for operation with completely transistorized circuits.

DATA

GENERAL:

CDITESTITUS.		
Operating Position		Any
Focusing Method		Electrostatic
Deflection Method		Electrostatic
Maximum Useful Image Area Diagonal		
measurement of 4 x 3 aspect ratio	0. 625 in.	
ELECTRICAL CHARACTERISTICS:	(a xx+ 100	***
Heater Voltage (AC or DC) Heater Current	6.3 V± 10%	
	0. 3 A	966
Spectral Response (See Fig. 4)	S-18	7522
Direct Interelectrode Capacities		**************************************
Signal Electrode to all others	4 uuf	
D1 to D2 (Horizontal Plates)	6 uuf	1
D3 to D4 (Vertical Plates)	6 uuf	
ABSOLUTE MAXIMUM RATINGS:		
Grid No. 1 Voltage		
Negative Bias	300 V	
Positive Bias	<u>0 V</u>	
Heater to Cathode Peak Voltage		
Heater Negative with Respect to Cathode	125 V	
Heater Positive with Respect to Cathode	0 V	
Grid No. 2 Voltage	750 V	1 7 1



ABSOLUTE	MAXIMUM	RATINGS,	Continued:
Faceplate	e		

Faceplate Illumination Temperature Signal Electrode Current TYPICAL OPERATION: Scanned Area O. 500 x 0. 375 Faceplate Temperature Optimum Signal Output Current (Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater O. 2 to 0. 5 ft-c Signal Electrode Voltage Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to O. 2 uA Grid No. 5 Voltage Focus Electrode Voltage Grid No. 2 and Grid No. 4 Voltage Grid No. 1 (For signal cutoff with no blanking
Signal Electrode Current 0.6 TYPICAL OPERATION: Scanned Area 0.500 x 0.375 Faceplate Temperature 30° to 35 Optimum Signal Output Current (Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater 0.5 to .05 to . Signal Electrode Voltage 20 to 16 Average Gamma of Transfer Characteristic over Signal Output Current Range of .05 to 0.2 uA Grid No. 5 Voltage 30 to 50 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 16 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 2 and Grid No. 4 Voltage 20 to 50 Grid No. 4 Volt
Signal Electrode Current 0. 6 TYPICAL OPERATION: Scanned Area 0. 500 x 0. 375 Faceplate Temperature 30° to 35 Optimum Signal Output Current (Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater 0. 2 to 0. 5 ft-c . 05 to . Signal Electrode Voltage 20 to 16 Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage 30 Focus Electrode Voltage 0 to 5 Grid No. 2 and Grid No. 4 Voltage 20
Scanned Area 0. 500 x 0. 373 Faceplate Temperature 30° to 35 Optimum Signal Output Current (Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater 0. 2 to 0. 5 ft-c Signal Electrode Voltage 20 to 16 Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage 30 Focus Electrode Voltage 0 to 5 Grid No. 2 and Grid No. 4 Voltage 26
Scanned Area 0. 500 x 0. 373 Faceplate Temperature 30° to 35 Optimum Signal Output Current (Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater 0. 2 to 0. 5 ft-c Signal Electrode Voltage 20 to 16 Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage 36 Focus Electrode Voltage 0 to 5 Grid No. 2 and Grid No. 4 Voltage 26
Faceplate Temperature Optimum Signal Output Current (Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater 0. 2 to 0. 5 ft-c Signal Electrode Voltage Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage Grid No. 5 Voltage Grid No. 2 and Grid No. 4 Voltage 30° to 35 30° to 35 0. 2 to 35 To 3
Optimum Signal Output Current (Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater 0. 2 to 0. 5 ft-c Signal Electrode Voltage Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage Focus Electrode Voltage Grid No. 2 and Grid No. 4 Voltage
(Less Dark Current, with uniform 2870° K Tungsten illumination on faceplate.) 5 ft-c and greater 0.2 to 0.5 ft-c .05 to . Signal Electrode Voltage 20 to 16 Average Gamma of Transfer Characteristic over Signal Output Current Range of .05 to 0.2 uA Grid No. 5 Voltage 30 Focus Electrode Voltage 0 to 5 Grid No. 2 and Grid No. 4 Voltage 20
Tungsten illumination on faceplate.) 5 ft-c and greater 0. 2 to 0.5 ft-c Signal Electrode Voltage Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage Focus Electrode Voltage Grid No. 2 and Grid No. 4 Voltage
5 ft-c and greater 0.1 0.2 to 0.5 ft-c .05 to . Signal Electrode Voltage 20 to 16 Average Gamma of Transfer Characteristic over Signal Output Current Range of .05 to 0.2 uA Grid No. 5 Voltage 30 Focus Electrode Voltage 0 to 5 Grid No. 2 and Grid No. 4 Voltage 26
O. 2 to 0. 5 ft-c .05 to . Signal Electrode Voltage .20 to 16 Average Gamma of Transfer Characteristic over Signal Output Current Range of .05 to 0. 2 uA Grid No. 5 Voltage .30 Focus Electrode Voltage .0 to .50 Grid No. 2 and Grid No. 4 Voltage .20
Signal Electrode Voltage Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage Focus Electrode Voltage Grid No. 2 and Grid No. 4 Voltage 20 to 10 30 30 30 30 30 30 30 30 30
Average Gamma of Transfer Characteristic over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage Focus Electrode Voltage Grid No. 2 and Grid No. 4 Voltage
over Signal Output Current Range of . 05 to 0. 2 uA Grid No. 5 Voltage Focus Electrode Voltage Grid No. 2 and Grid No. 4 Voltage 20
0. 2 uAGrid No. 5 Voltage30Focus Electrode Voltage0 to 3Grid No. 2 and Grid No. 4 Voltage20
Focus Electrode Voltage 0 to 5 Grid No. 2 and Grid No. 4 Voltage 20
Focus Electrode Voltage 0 to 5 Grid No. 2 and Grid No. 4 Voltage 20
Grid No. 2 and Grid No. 4 Voltage
on G1) -45 <u>to -1</u> (
Minimum Blanking Voltage (Peak to Peak)
When applied to Grid No. 1
When applied to Cathode
Deflection Voltages (Peak to Peak)
Horizontal (D1 to D2)
Vertical (D3 to D4)
Horizontal Plates DC Voltage 200 V to 25
Vertical Plates DC Voltage 200 V to 25

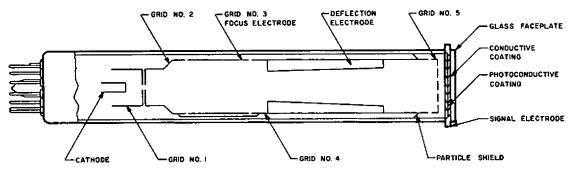


FIG. I



PRINCIPLES OF OPERATION

Basic Vidicon Operation

The GEC 7522 vidicon is a photoconductive imaging device using electrostatic focus and deflection. The vidicon faceplate inside surface is coated with a transparent conductive coating as shown in Figure 1. Over this a layer of photoconductive material is deposited. This material when dark is a reasonably good insulator but increases in electrical conductivity when exposed to light. The electron beam scans the back surface of this photoconductor.

In operation, the photoconductor front surface is held at a positive potential with respect to the cathode, by applying voltage to the transparent conductive coating. The scanning electron beam deposits a negative charge on the photoconductor back surface. Where the photoconductor is dark and its resistance high, a negative charge accumulates until the back surface reaches cathode potential.

Where light from the scene falls on the photoconductor, conductivity increases, reducing negative charge at the illuminated point. Negative charge reduction at any point is proportional to the illumination on that point. The photoconductor therefore becomes charged much like a capacitor in a pattern conforming to the scene image. As the electron beam scans the photoconductor, it will release electrons into the less negatively charged areas and the resultant varying electron flow through a load resistor constitutes the video signal.

The vidicon has the ability to store the image for an entire scanning cycle. The image is "photographed" in a pattern of varying charge on the photoconductor back surface and is accumulated there for one complete frame. By this process the vidicon produces usable signal output from dimly lighted scenes.

Field Correction

A special mesh electrode, G5, is incorporated in the 7522 to assure flat field output and to compensate for beam landing error and optical lens distortion. The potential of this mesh can be varied independently of the other electrodes.

Focus

Electrostatic focus is accomplished in a saddle field lens arrangement composed of G2, G3, and G4, with G3 as the variable focusing electrode.

Deflection

Electrostatic deflection in the 7522 is accomplished through the use of a specially designed deflection plate configuration called the Deflectron. The conventional crossed pair deflection plates causes the electron beam to be deflected sequentially; that is,



PRINCIPLES OF OPERATION, Continued:

in passing between the first set of plates it is deflected in one plane and then when reaching the second set of plates is deflected in the other plane. The Deflectron causes the beam to be deflected both horizontally and vertically simultaneously as in magnetic deflection. This common center of deflection reduces the undesirable effects of fringe fields, defocusing and other distortion found in conventional deflection plate scanning.

Physically the Deflectron is a tube of insulating material, the inside of which contains the printed deflection plate pattern. The pattern of the Deflectron is illustrated laid out on a flat plane in Fig. 2. If the pattern is rolled to connect Side A to Side B, four individual electrical paths can be traced.

OPERATING CONSIDERATIONS

Installation

The GEC 7522 may be operated in any position, however, it must be oriented to place the horizontal deflection axis parallel to the horizontal image plane. The horizontal deflection axis is essentially parallel to a line through base pins 2 and 9. (See Fig. 7) The 13 pin socket for the 7522 is Type GEC 52-01 or equivalent.

Shielding

The 7522 should be shielded during operation from the effects of stray magnetic or electrostatic fields by the use of a suitable magnetic shield.

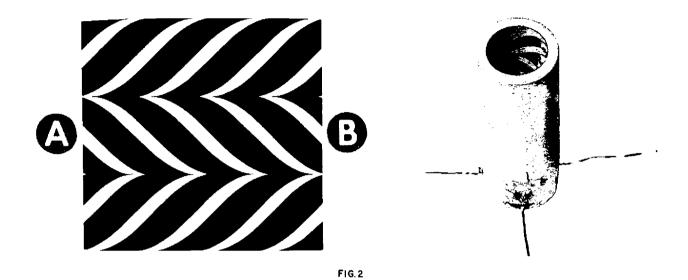
Deflection Circuits

The 7522 may be driven by standard electrostatic deflection circuits incorporating DC centering. The Deflectron elements are operated at a variable DC potential of from 200 to 250 volts positive with respect to cathode which will permit critical adjustment for minimum astigmatism.

Video Amplifier

The video amplifier design for use with the 7522 should incorporate all of the characteristics of an amplifier for a standard vidicon low noise, high gain, aperture correction and high peaking. A typical transistor video preamplifier is shown in Fig. 3.





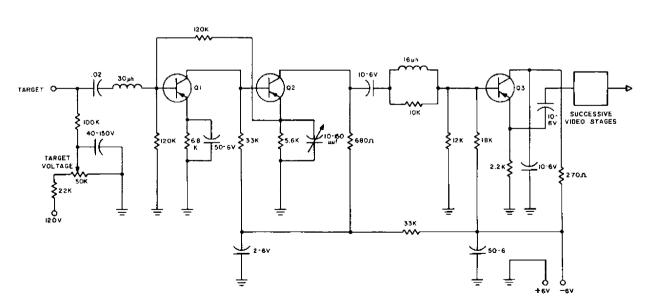
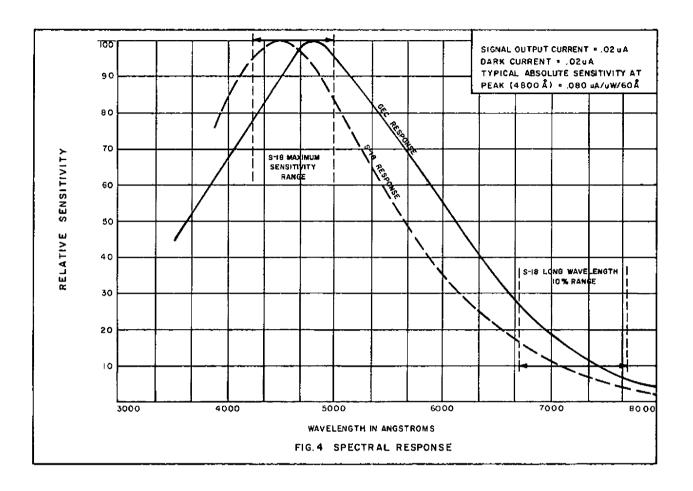
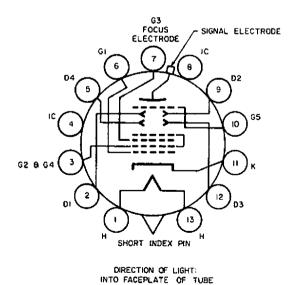


FIG. 3 TYPICAL TRANSISTOR VIDEO PRE-AMPLIFIER







HEATER PIN II DI HORIZONTAL DEFLECTION PLATE PIN 2: GRID NO. 2 8. 4 PIN 4: INTERNAL CONNECTION -- DO NOT USE PIN 5: D4 VERTICAL DEFLECTION PLATE PIN 6: GRID NO. I G3 FOCUS ELECTRODE PIN 7: INTERNAL CONNECTION -- DO NOT USE PIN 8: PIN 9: D2 HORIZONTAL DEFLECTION PLATE PIN IO GRID NO. 5 PIN II: CATHODE PIN 12: D3 VERTICAL DEFLECTION PLATE PIN 13: HEATER SHORT INDEX PIN: INTERNAL CONNECTION -- DO NOT USE FLANGE: SIGNAL ELECTRODE

FIG. 5